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(54) **Title:** SELECTIVE DEPOSITION OF ALUMINUM-CONTAINING DIELECTRIC MATERIAL ON DIELECTRIC OVER METAL UTILIZING ALKYNES

Step 1: Surface Pre-clean



Step 2: Metal Passivation



Step 3: DoD Selective Dep

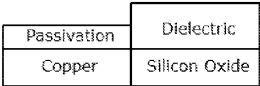


FIG. 1

(57) **Abstract:** A method for selectively passivating a surface of a substrate, wherein the surface of the substrate includes at least a first surface comprising a metal and at least a second surface comprising a dielectric material. The method includes the step of exposing the surface to at least one alkyne wherein the alkyne selectively reacts with the metal to passivate the first surface thereby leaving the second surface substantially unreacted.

[Continued on next page]

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